

Title (en)  
CATALYST INFLUENCED PATTERN TRANSFER TECHNOLOGY

Title (de)  
KATALYSATORBEEINFLUSSTE STRUKTURÜBERTRAGUNGSTECHNIK

Title (fr)  
TECHNOLOGIE DE TRANSFERT DE MOTIF INFLUENCÉ PAR UN CATALYSEUR

Publication  
**EP 3718133 A4 20211124 (EN)**

Application  
**EP 18884487 A 20181109**

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- US 201862701049 P 20180720
- US 201862729361 P 20180910
- US 2018060176 W 20181109

Abstract (en)  
[origin: WO2019108366A1] Various embodiments of the present technology generally relate to semiconductor device architectures and manufacturing techniques. More specifically, some embodiments of the present technology relate to silicon etching using catalyst influenced chemical etching technology with application to three-dimensional memory architectures and transistors. CICE is a catalyst based etching method that can be used on semiconductors as well as multilayers of the semiconductors. Various embodiments of the CICE process can use a catalyst to etch semiconducting substrates and to fabricate high aspect ratio features. A fabrication tool for this purpose is also disclosed. This shall enable adoption of this technology in making semiconductor devices.

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Citation (search report)

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- See also references of WO 2019108366A1

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